# **OSRAM** LE BR Q7WM **Datasheet**

Discontinued

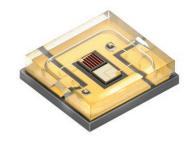




# OSRAM OSTAR® Projection Compact

# LE BR Q7WM

Compact light source in SMT technology, glass window on top, RoHS compliant







## **Applications**

- Projection & Display

- Visualization

#### **Features**

- Package: compact lightsource in SMT technology with glass window on top
- Chip technology: Thinfilm / ThinGaN
- Typ. Radiation: 120° (Lambertian emitter)
- Color:  $\lambda_{dom}$  = 460 nm (• blue);  $\lambda_{dom}$  = 617 nm (• red)
- Corrosion Robustness Class: 3B
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM)

### **Ordering Information**

Type	Brightness 1)	Ordering Code
LE BR Q7WM-TG	TI-24+JXJZ-23	Q65112A7832
• blue	• $\Phi_E$ = 280 450 mW (I <sub>F</sub> = 350 mA)	
• red	• Φ <sub>V</sub> = 45 71 lm (I <sub>E</sub> = 350 mA)	

#### LE BR Q7WM DATASHEET



# **Ordering Information**

Type Brightness 1) Ordering Code



<b>Maximum</b>	Ratings
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Maximum Ratingo				
Parameter	Symbol		Values ● blue	Values • red
Operating Temperature	T <sub>op</sub>	min.	-40 °C	-40 °C
	оp	max.	85 °C	85 °C
Storage Temperature	T <sub>stg</sub>	min.	-40 °C	-40 °C
	olg	max.	85 °C	85 °C
Junction Temperature	T <sub>j</sub>	max.	125 °C	125 °C
Forward Current	I <sub>F</sub>	min.	20 mA	20 mA
$T_j = T_{j \text{ max.}}$	·	max.	500 mA	500 mA
Forward Current pulsed f = 240Hz; D = 0.5; T <sub>i</sub> = T <sub>imax</sub>	F pulse		1000 mA	1000 mA
Surge Current	I <sub>FS</sub>	max.	1500 mA	1500 mA
$t \le 10 \mu s; D = 0.5; T_j = T_{j \text{ max.}}$	10			
ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 (HBM)	$V_{ESD}$		2 kV	2 kV
Reverse current 2)	I <sub>R</sub>	max.	200 mA	200 mA

## **Characteristics**

 $I_F = 350 \text{ mA}; T_S = 25 \text{ °C}$ 

Parameter	Symbol		Values ● blue	Values • red
Peak Wavelength	$\lambda_{peak}$	typ.	460 nm	624 nm
Dominant Wavelength 3)	$\lambda_{\sf dom}$	min.	450 nm	610 nm
	dom	typ.	460 nm	617 nm
		max.	465 nm	622 nm
Spectral bandwidth at 50% I <sub>rel,max</sub>	$\Delta \lambda$	typ.	19 nm	18 nm
Viewing angle at 50% $\rm I_{\rm \scriptscriptstyle V}$	2φ	typ.	120 °	120 °
Radiating surface	$A_{color}$	typ.	0.65 x 0.65	0.65 x 0.65
	COIOI		mm²	mm²
Partial Flux acc. CIE 127:2007 4)	Ф <sub>Е/V, 120°</sub>	typ.	0.82	0.82
$\Phi_{\text{E/V }120^{\circ}} = \text{x * } \Phi_{\text{E/V }180^{\circ}}$	L/ V , 120			
Forward Voltage 5)	V <sub>F</sub>	min.	2.70 V	2.00 V
$I_{\rm F} = 350  \text{mA}$	•	typ.	3.40 V	2.30 V
		max.	3.70 V	2.70 V
Reverse voltage (ESD device)	V <sub>R ESD</sub>	min.	5 V	5 V
Reverse voltage 2)	$V_R$	max.	1.2 V	1.2 V
I <sub>R</sub> = 20 mA	TX			
Real thermal resistance junction/solderpoint <sup>6)</sup>	R <sub>thJS real</sub>	typ.	16 K / W	14 K / W
1 Chip on	tiloo real	max.	19 K / W	17 K / W
Electrical thermal resistance junction/solderpoint <sup>6)</sup>	R <sub>thJS elec.</sub>	typ.	11 K / W	10 K / W
1 Chip on	1100 0100.	max.	13 K / W	12 K / W
with efficiency $\eta e = 29 \%$ (blue); 27 % (red)				



# **Brightness Groups**

• blue

Group	Radiant Flux <sup>1)</sup> I <sub>F</sub> = 350 mA min. Φ <sub>E</sub>	Radiant Flux <sup>1)</sup> I <sub>F</sub> = 350 mA max. Φ <sub>E</sub>	
TG	280 mW	330 mW	
TH	330 mW	390 mW	
TI	390 mW	450 mW	

# **Brightness Groups**

• red

Group	Luminous Flux <sup>1)</sup> $I_F = 350 \text{ mA}$ min. $\Phi_V$	Luminous Flux $^{1)}$ $I_F = 350 \text{ mA}$ max. $\Phi_V$	
JX	45 lm	52 lm	
JY	52 lm	61 lm	
JZ	61 lm	71 lm	



# **Wavelength Groups**

• blue

Group	Dominant Wavelength 3)	Dominant Wavelength 3)
	min.	max.
	$\lambda_{\sf dom}$	$\lambda_{\sf dom}$
2	450 nm	455 nm
3	455 nm	460 nm
4	460 nm	465 nm

# **Wavelength Groups**

• red

Group	Dominant Wavelength 3)	Dominant Wavelength 3)
	min.	max.
	$\lambda_{dom}$	$\lambda_{dom}$
2	610 nm	616 nm
3	616 nm	622 nm

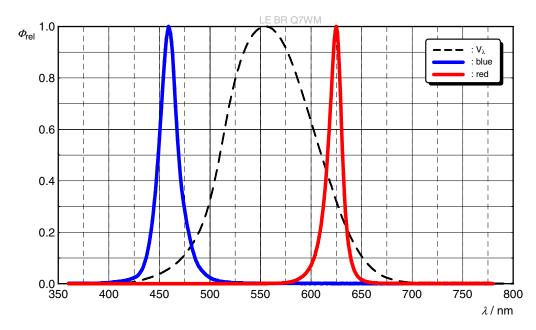
## **Group Name on Label**

Example: TG-2+JX-2

Color	Brightness	Wavelength
• blue	TG	2
• red	JX	2

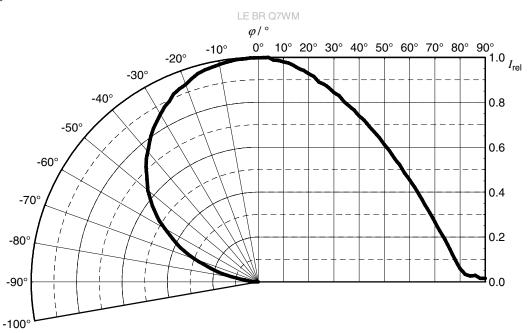
## Relative Spectral Emission 4)

$$\Phi_{rel}$$
 = f ( $\lambda$ ); I<sub>F</sub> = 350 mA; T<sub>J</sub> = 25 °C



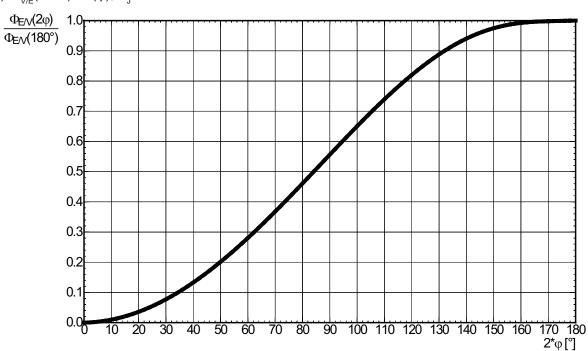
#### Radiation Characteristics 4)

$$I_{rel} = f (\phi); T_J = 25 °C$$



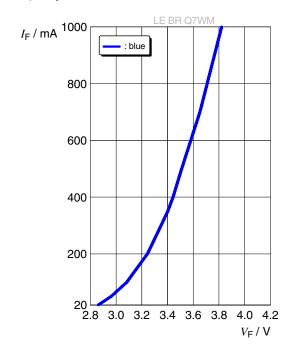
### Relative Partial Flux 4)

 $\Phi_{_{\text{V/E}}}(2\phi)/\Phi_{_{\text{V/E}}}(180^\circ) = f(\phi); \, T_{_J} = 25 \,\, ^\circ C$ 



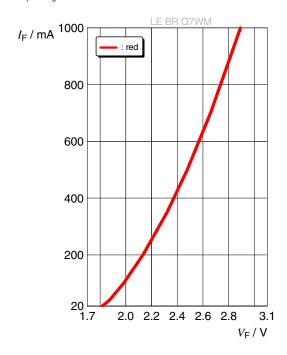
#### Forward current 4), 7)

$$I_F = f(V_F); T_J = 25 °C$$



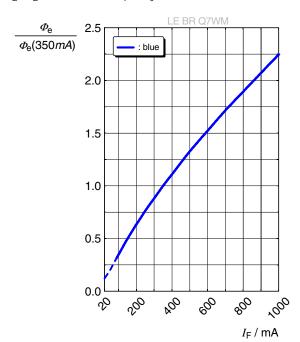
#### Forward current 4), 7)

$$I_F = f(V_F); T_J = 25 \, ^{\circ}C$$



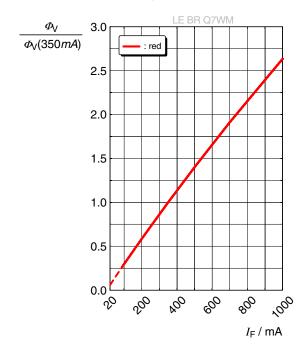
## Relative Radiant Power 4), 7)

$$\Phi_{\rm F}/\Phi_{\rm F}(350~{\rm mA}) = f(I_{\rm F}); T_{\rm J} = 25~{\rm ^{\circ}C}$$



## Relative Luminous Flux 4), 7)

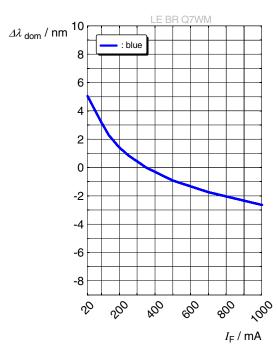
$$\Phi_{V}/\Phi_{V}(350 \text{ mA}) = f(I_{F}); T_{J} = 25 \text{ °C}$$





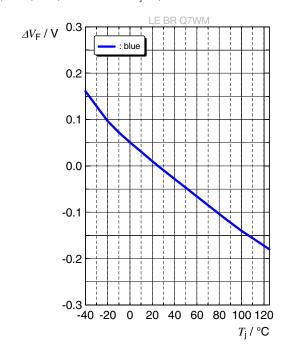
# Dominant Wavelength 4)

$$\Delta\lambda_{dom} = f(I_F); T_J = 25 \text{ }^{\circ}\text{C}$$



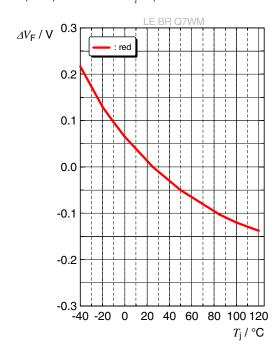
## Forward Voltage 4)

$$\Delta V_{F} = V_{F} - V_{F}(25 \text{ °C}) = f(T_{i}); I_{F} = 350 \text{ mA}$$



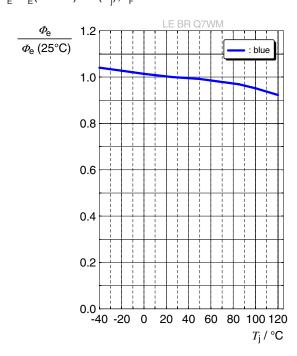
## Forward Voltage 4)

$$\Delta V_{F} = V_{F} - V_{F}(25 \text{ °C}) = f(T_{i}); I_{F} = 350 \text{ mA}$$



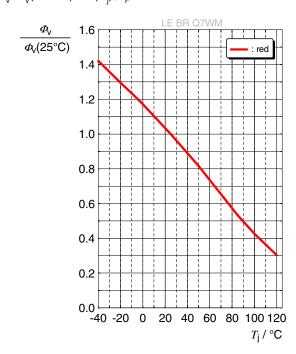
#### Relative Radiant Power 4)

$$\Phi_{F}/\Phi_{F}(25 \text{ °C}) = f(T_{i}); I_{F} = 350 \text{ mA}$$



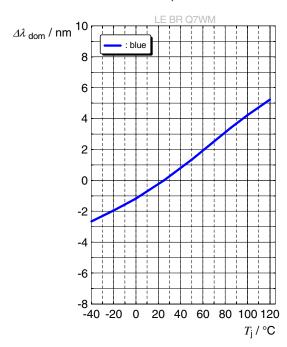
#### Relative Luminous Flux 4)

$$\Phi_{v}/\Phi_{v}(25 \text{ °C}) = f(T_{i}); I_{F} = 350 \text{ mA}$$



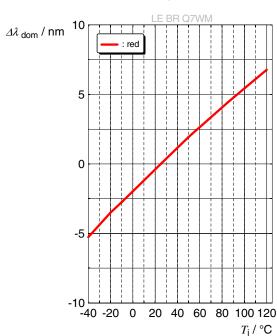
## Dominant Wavelength 4)

$$\Delta \lambda_{dom} = \lambda_{dom} - \lambda_{dom} (25 \text{ °C}) = f(T_j); I_F = 350 \text{ mA}$$



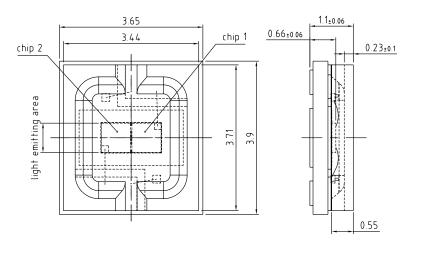
## Dominant Wavelength 4)

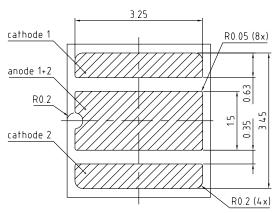
$$\Delta \lambda_{\text{dom}} = \lambda_{\text{dom}} - \lambda_{\text{dom}} (25 \text{ °C}) = f(T_j); I_F = 350 \text{ mA}$$





## **Dimensional Drawing** 8)





general tolerance ±0.1 lead finish Au

C67062-A0205-A1KA-04

#### **Further Information:**

**Approximate Weight:** 46.0 mg

**Corrosion test:** Class: 3B

Test condition: 40°C / 90 % RH / 15 ppm H<sub>2</sub>S / 14 days (stricter than IEC

60068-2-43)

**ESD** advice: The device is protected by ESD device which is connected in parallel to the

Chip.



### **Electrical Internal Circuit**

Pin Assignment:

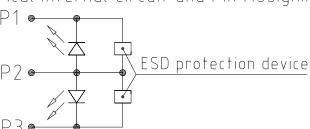
P1: cathode chip 1

P2 : anode chip 1 + chip 2

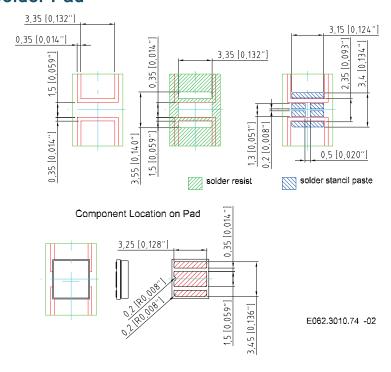
P3: cathode chip 2

Chip 1 : Blue Chip 2 : Red

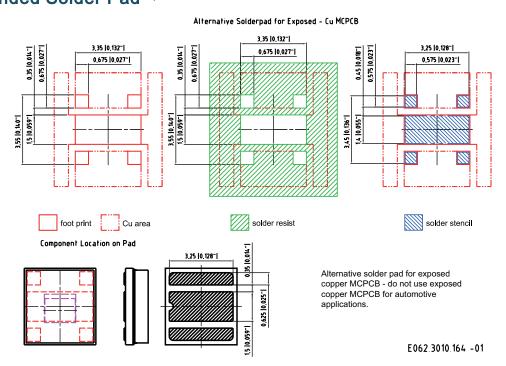
Electrical Internal Circuit and Pin Assignment



#### Recommended Solder Pad 8)



#### Recommended Solder Pad 8)

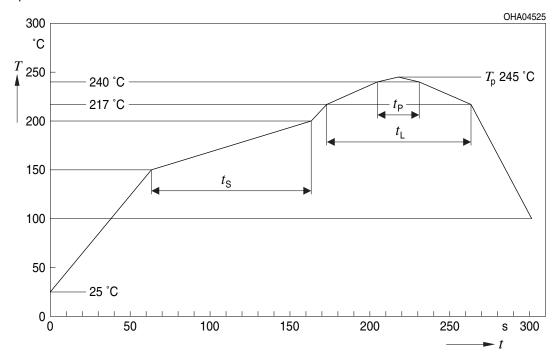


Exposed Copper MCPCB must not exceed thickness of 1mm. For superior solder joint connectivity results we recommend soldering under standard nitrogen atmosphere. Package not suitable for any kind of wet cleaning or ultrasonic cleaning. In any case the solder pad design shall be validated under customer application conditions.



## **Reflow Soldering Profile**

Product complies to MSL Level 2 acc. to JEDEC J-STD-020E

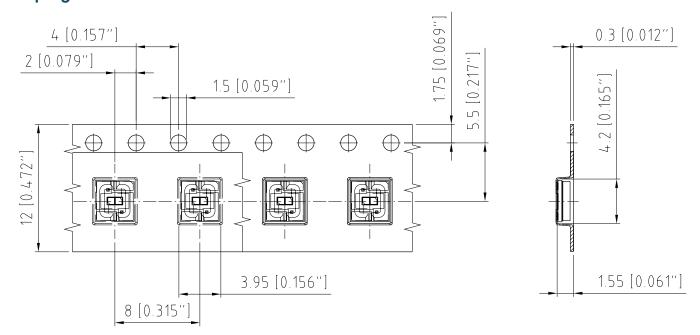


Profile Feature	Symbol	Pb	-Free (SnAgCu) Ass	sembly	Unit
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat*) 25 °C to 150 °C			2	3	K/s
Time t <sub>s</sub> T <sub>Smin</sub> to T <sub>Smax</sub>	t <sub>s</sub>	60	100	120	S
Ramp-up rate to peak $^{*)}$ T <sub>Smax</sub> to T <sub>P</sub>			2	3	K/s
Liquidus temperature	$T_{L}$		217		°C
Time above liquidus temperature	$t_{\scriptscriptstyle L}$		80	100	S
Peak temperature	T <sub>P</sub>		245	260	°C
Time within 5 °C of the specified peak temperature T <sub>P</sub> - 5 K	t <sub>P</sub>	10	20	30	S
Ramp-down rate* T <sub>P</sub> to 100 °C			3	6	K/s
Time 25 °C to T <sub>P</sub>				480	S

All temperatures refer to the center of the package, measured on the top of the component

 $<sup>^{\</sup>star}$  slope calculation DT/Dt: Dt max. 5 s; fulfillment for the whole T-range

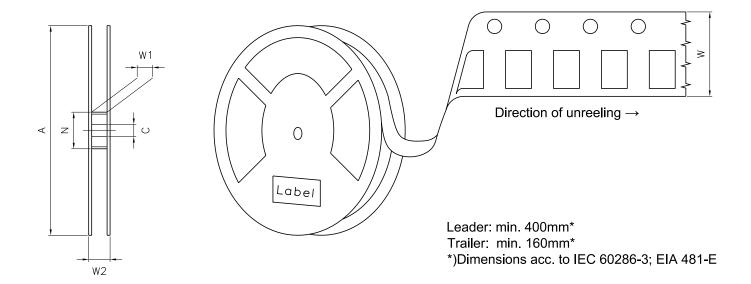
# Taping 8)



C63062-A4059-B5-03



## Tape and Reel 9)

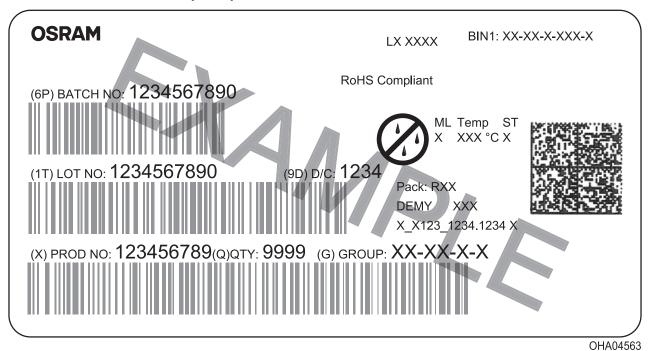


### **Reel Dimensions**

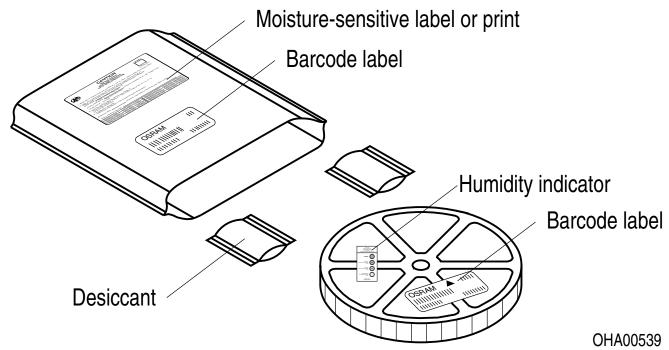
Α	W	$N_{\min}$	$W_1$	$W_{2  \text{max}}$	Pieces per PU
180 mm	12 + 0.3 / - 0.1 mm	60 mm	12.4 + 2 mm	18.4 mm	500



## **Barcode-Product-Label (BPL)**



## Dry Packing Process and Materials 8)



Moisture-sensitive product is packed in a dry bag containing desiccant and a humidity card according JEDEC-STD-033.

#### **Notes**

The evaluation of eye safety occurs according to the standard IEC 62471:2006 (photo biological safety of lamps and lamp systems). Within the risk grouping system of this IEC standard, the device specified in this data sheet fall into the class **moderate risk (exposure time 0.25 s)**. Under real circumstances (for exposure time, conditions of the eye pupils, observation distance), it is assumed that no endangerment to the eye exists from these devices. As a matter of principle, however, it should be mentioned that intense light sources have a high secondary exposure potential due to their blinding effect. When looking at bright light sources (e.g. headlights), temporary reduction in visual acuity and afterimages can occur, leading to irritation, annoyance, visual impairment, and even accidents, depending on the situation.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit https://ams-osram.com/support/application-notes

#### **Disclaimer**

#### Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on our website.

#### **Packing**

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

#### Product and functional safety devices/applications or medical devices/applications

Our components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

Our products are not qualified at module and system level for such application.

In case buyer – or customer supplied by buyer – considers using our components in product safety devices/applications or medical devices/applications, buyer and/or customer has to inform our local sales partner immediately and we and buyer and /or customer will analyze and coordinate the customer-specific request between us and buyer and/or customer.



#### Glossary

- Brightness: Brightness values are measured during a current pulse of typically 25 ms, with an internal reproducibility of ±8 % and an expanded uncertainty of ±11 % (acc. to GUM with a coverage factor of k = 3).
- Reverse Operation: This product is intended to be operated applying a forward current within the specified range. Applying any continuous reverse bias or forward bias below the voltage range of light emission shall be avoided because it may cause migration which can change the electro-optical characteristics or damage the LED.
- Wavelength: The wavelength is measured at a current pulse of typically 25 ms, with an internal reproducibility of ±0.5 nm and an expanded uncertainty of ±1 nm (acc. to GUM with a coverage factor of k = 3).
- Typical Values: Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- Forward Voltage: Forward voltages are tested at a current pulse duration of 1 ms and a tolerance of ±0.05 V and an expanded uncertainty of ±0.1 V (acc. to GUM with a coverage factor of k = 3).
- <sup>6)</sup> Thermal Resistance: Rth max is based on statistic values (6σ) used for Derating.
- Characteristic curve: In the range where the line of the graph is broken, you must expect higher differences between single devices within one packing unit.
- Tolerance of Measure: Unless otherwise noted in drawing, tolerances are specified with ±0.1 and dimensions are specified in mm.
- 9) Tape and Reel: All dimensions and tolerances are specified acc. IEC 60286-3 and specified in mm.

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Revision History		
Version	Date	Change
1.7	2018-12-19	Wavelength Groups Characteristics
1.8	2020-04-16	Dimensional Drawing Schematic Transportation Box Dimensions of Transportation Box
1.9	2020-07-09	Wavelength Groups
1.10	2020-10-06	Maximum Ratings
1.11	2020-12-16	Characteristics
1.12	2021-01-25	Wavelength Groups
1.13	2021-09-23	Recommended Solder Pad
1.13	2023-05-23	Recommended Solder Pad New Layout Applications
1.14	2023-05-23	Discontinued

#### Discontinued



EU RoHS and China RoHS compliant product 此产品符合欧盟 RoHS 指令的要求; 按照中国的相关法规和标准, 不含有毒有害物质或元素。

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